

AMENDMENT UNDER 37 C.F.R. § 1.111
U.S. Appl. No. 09/161,699

19. (Amended) The two-dimensional active-matrix type light-emitting device as set forth in claim 14, wherein the ferroelectric gate field-effect transistor comprises a single ferroelectric gate field-effect transistor per pixel.

20. (Amended) The two-dimensional active-matrix type light-emitting device as set forth in any one of claims 8-11 and 15, wherein the ferroelectric gate field-effect transistor comprises a single ferroelectric gate field-effect transistor per pixel.

21. (Amended) The two-dimensional active-matrix type light-emitting device as set forth in claim 16, wherein the ferroelectric gate field-effect transistor comprises a single ferroelectric gate field-effect transistor per pixel.

C1
CMT
22. (Amended) The two-dimensional active-matrix type light-emitting device as set forth in any one of claims 2-6 and 12, wherein the ferroelectric gate field-effect transistor consists of a single type of semiconductor selected from one of an n-type and a p-type semiconductor.

23. (Amended) The two-dimensional active-matrix type light-emitting device as set forth in claim 13, wherein the ferroelectric gate field-effect transistor consists of a single type of semiconductor selected from one of an n-type and a p-type semiconductor.

24. (Amended) The two-dimensional active-matrix type light-emitting device as set forth in claim 14, wherein the ferroelectric gate field-effect transistor consists of a single type of semiconductor selected from one of an n-type and a p-type semiconductor.

25. (Amended) The two-dimensional active-matrix type light-emitting device as set forth in any one of claims 8-11 and 15, wherein the ferroelectric gate field-effect transistor

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consists of a single type of semiconductor selected from one of an n-type and a p-type semiconductor.

C1
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²⁷~~26~~ (Amended) The two-dimensional active-matrix type light-emitting device as set
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forth in claim ~~16~~, wherein the ferroelectric gate field-effect transistor consists of a single type of
semiconductor selected from one of an n-type and a p-type semiconductor.
